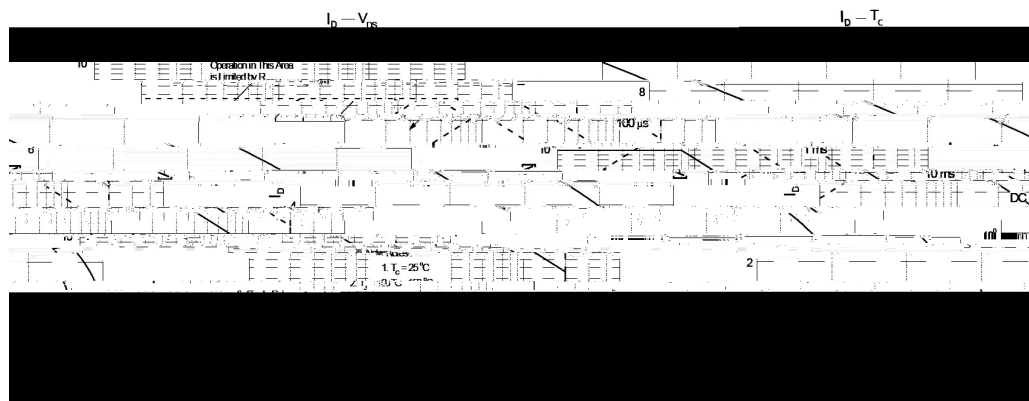
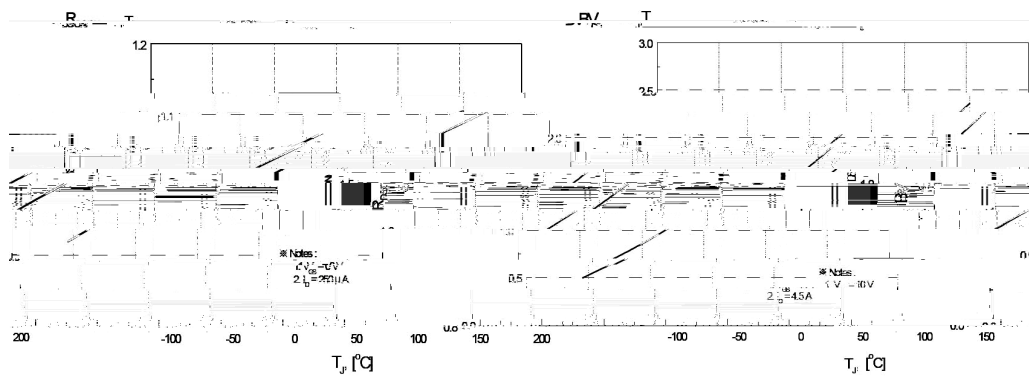
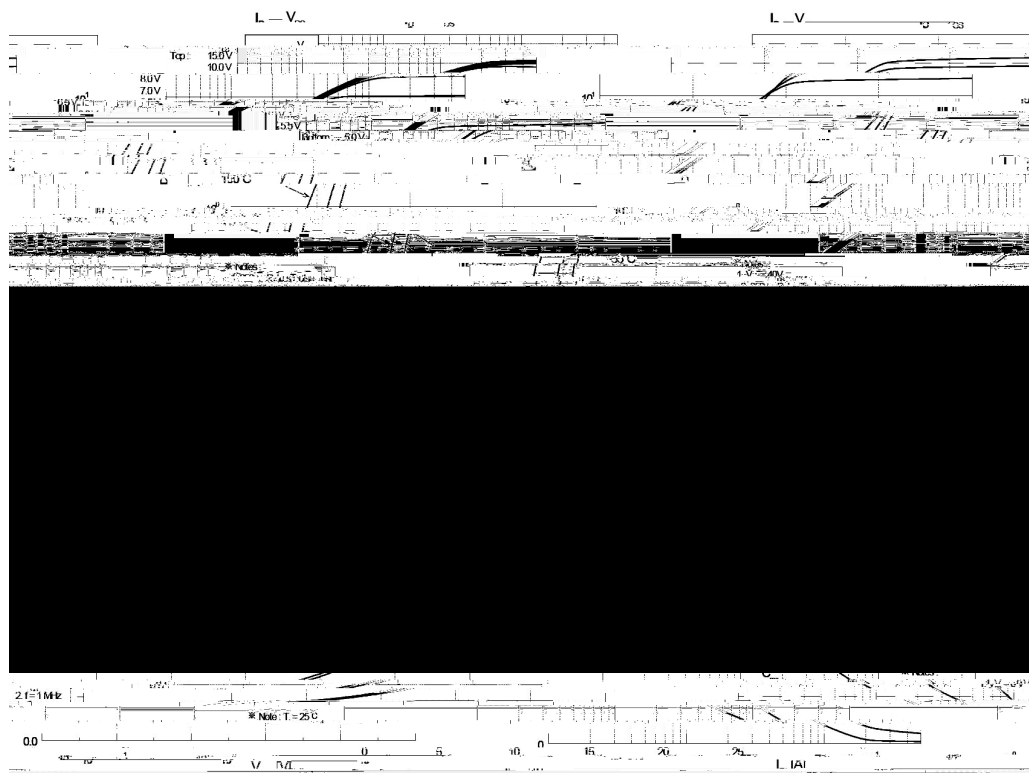


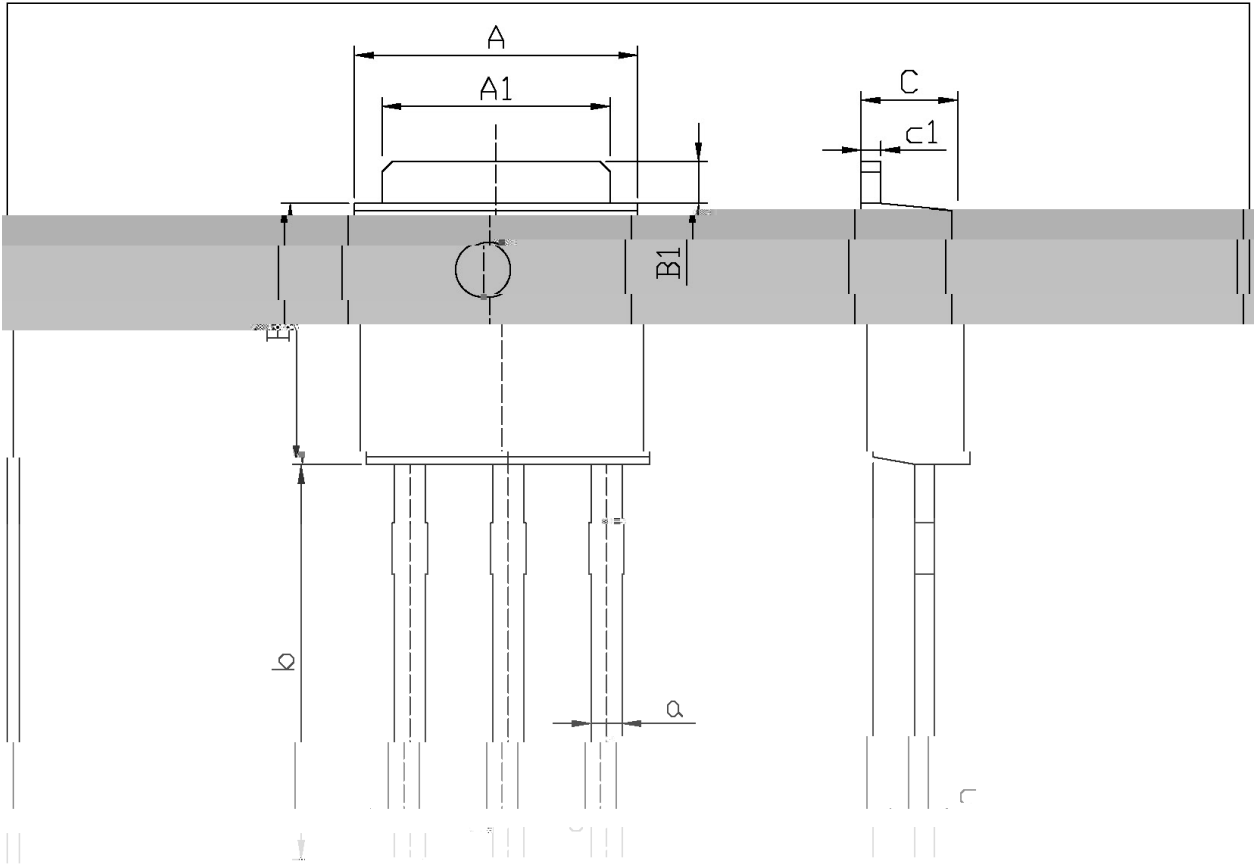
Rev.D Nov.-2015

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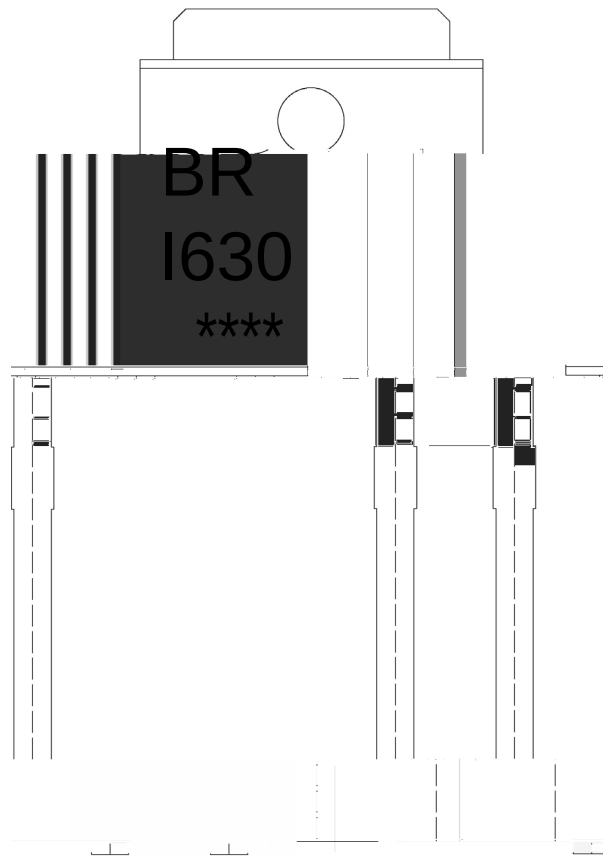
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	200	V
Drain Current	$I_{D(TC=25)}$	9	A
Drain Current	$I_{D(TC=100)}$	5.7	A
Drain Current - Pulsed	I_{DM}	36	A
Gate-Source Voltage	V_{GSS}	± 30	V
Avalanche Current	I_{AR}	9	A
Single Pulsed Avalanche Energy	E_{AS}	160	mJ
Repetitive Avalanche Energy	E_{AR}	7.2	mJ
Power Dissipation	P_D	3.13	W
Power Dissipation	$P_D(TC=25)$	72	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	200			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=200V$ $V_{GS}=0V$			10	μA
		$V_{DS}=160V$ $T_C=125$			100	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=4.5A$		0.34	0.4	Ω
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=4.5A$		7.05		S
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=9A$			1.5	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1MHz$		550	720	pF
Output Capacitance	C_{oss}			85	110	pF
Reverse Transfer Capacitance	C_{rss}			22	29	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=100V$ $I_D=9A$ $R_G=25\Omega$		11	30	ns
Turn-On Rise Time	t_r			70	150	ns
Turn-Off Delay Time	$t_{d(off)}$			60	130	ns
Turn-Off Fall Time	t_f			65	140	ns





A						
6.45						
6.75						
a						
0.50						
0.70						
B						
5.95						
6.25						
C						
0.45						
0.55						
B1						
0.95						
1.25						
C1						
0.45						
0.55						



BR

I630

Note:

BR: Company Code

I630: Product Type.

****: Lot No. Code, code change with Lot No.

